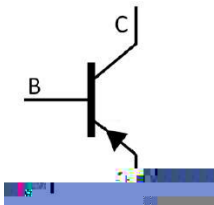


Silicon PNP transistor in a TO-92 Plastic Package.

Low current, Low voltage.

General purpose amplifier.

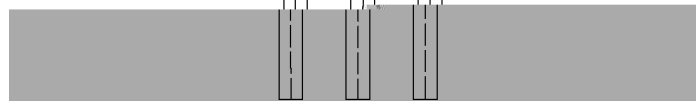
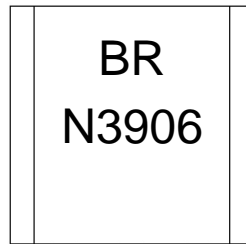


PIN 1 Collector PIN 2 Base PIN 3 Emitter

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-200	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-10\mu A$ $I_E=0$	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-1.0mA$ $I_B=0$	-40			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-10\mu A$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-40V$ $I_E=0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-1.0V$ $I_C=-10mA$	100		300	
	$h_{FE(2)}$	$V_{CE}=-1.0V$ $I_C=-100mA$	30			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-50mA$ $I_B=-5.0mA$			-0.4	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-50mA$ $I_B=-5.0mA$			-0.95	V
Current Gain Bandwidth Product	f_T	$I_C=-10mA$ $f=100MHz$ $V_{CE}=-20V$	250			MHz
Output Capacitance	C_{ob}	$V_{CB}=-5.0V$ $I_E=0$ $f=100KHz$			4.5	pF
Turn On Time	T_{on}	$V_{CC}=-3.0V$ $I_C=-10mA$ $V_{BE}=-0.5V$ $I_{B1}=-1.0mA$			0.07	μs
Turn Off Time	T_{off}	$V_{CC}=-3.0V$ $I_C=-10mA$ $I_{B1}=-I_{B2}=-1.0mA$			0.3	μs

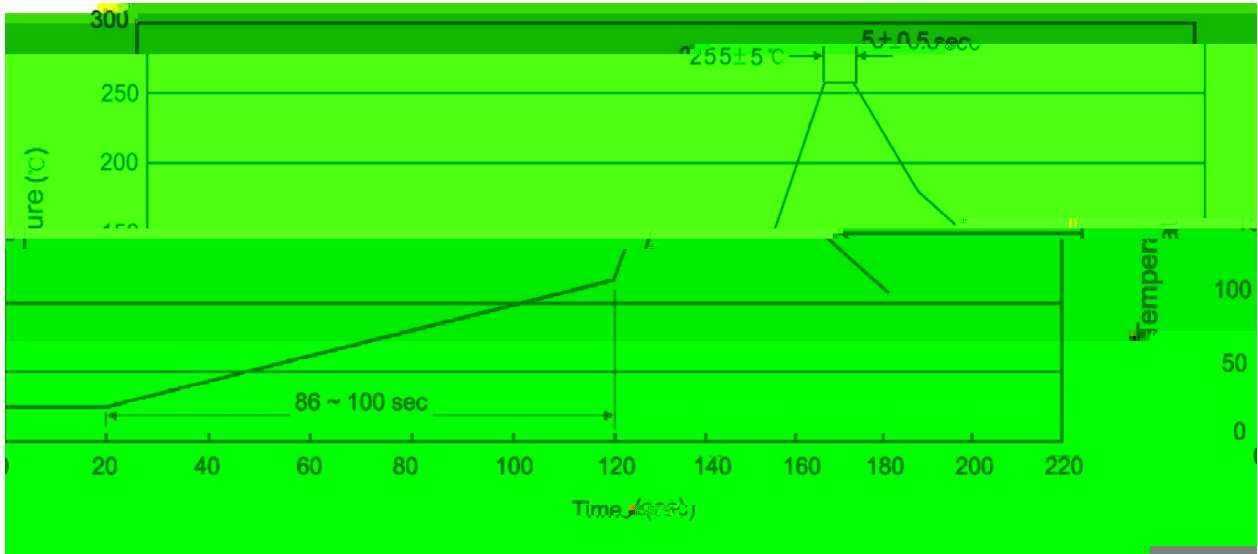


Note:

BR: Company Code.

N3906: Product Type.

****: Lot No. Code, code change with Lot No.


Note:

- | | | | | | |
|---|-----|-----|----|----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255 | 5 | 5 | 0.5sec; | 2.Peak Temp.:255 5 , Duration:5 0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

270 5

10 1 sec.

Temp.:270±5

Time:.(pe.9c408Tf13.2(i)-1.2(me:6/TT